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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	376
Number of Gates	526000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200efc484-3

Table 5. APEX 20K FineLine BGA Package Options & I/O Count *Notes (1), (2)*

Device	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
EP20K30E	93	128			
EP20K60E	93	196			
EP20K100		252			
EP20K100E	93	246			
EP20K160E			316		
EP20K200			382		
EP20K200E			376	376	
EP20K300E				408	
EP20K400				502 (3)	
EP20K400E				488 (3)	
EP20K600E				508 (3)	588
EP20K1000E				508 (3)	708
EP20K1500E					808

Notes to Tables 4 and 5:

- (1) I/O counts include dedicated input and clock pins.
- (2) APEX 20K device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), 1.27-mm pitch ball-grid array (BGA), 1.00-mm pitch FineLine BGA, and pin-grid array (PGA) packages.
- (3) This device uses a thermally enhanced package, which is taller than the regular package. Consult the *Altera Device Package Information Data Sheet* for detailed package size information.

Table 6. APEX 20K QFP, BGA & PGA Package Sizes

Feature	144-Pin TQFP	208-Pin QFP	240-Pin QFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
Pitch (mm)	0.50	0.50	0.50	1.27	1.27	—
Area (mm ²)	484	924	1,218	1,225	2,025	3,906
Length × Width (mm × mm)	22 × 22	30.4 × 30.4	34.9 × 34.9	35 × 35	45 × 45	62.5 × 62.5

Table 7. APEX 20K FineLine BGA Package Sizes

Feature	144 Pin	324 Pin	484 Pin	672 Pin	1,020 Pin
Pitch (mm)	1.00	1.00	1.00	1.00	1.00
Area (mm ²)	169	361	529	729	1,089
Length × Width (mm × mm)	13 × 13	19 × 19	23 × 23	27 × 27	33 × 33

General Description

APEX™ 20K devices are the first PLDs designed with the MultiCore architecture, which combines the strengths of LUT-based and product-term-based devices with an enhanced memory structure. LUT-based logic provides optimized performance and efficiency for data-path, register-intensive, mathematical, or digital signal processing (DSP) designs. Product-term-based logic is optimized for complex combinatorial paths, such as complex state machines. LUT- and product-term-based logic combined with memory functions and a wide variety of MegaCore and AMPP functions make the APEX 20K device architecture uniquely suited for system-on-a-programmable-chip designs. Applications historically requiring a combination of LUT-, product-term-, and memory-based devices can now be integrated into one APEX 20K device.

APEX 20KE devices are a superset of APEX 20K devices and include additional features such as advanced I/O standard support, CAM, additional global clocks, and enhanced ClockLock clock circuitry. In addition, APEX 20KE devices extend the APEX 20K family to 1.5 million gates. APEX 20KE devices are denoted with an “E” suffix in the device name (e.g., the EP20K1000E device is an APEX 20KE device). [Table 8](#) compares the features included in APEX 20K and APEX 20KE devices.

Functional Description

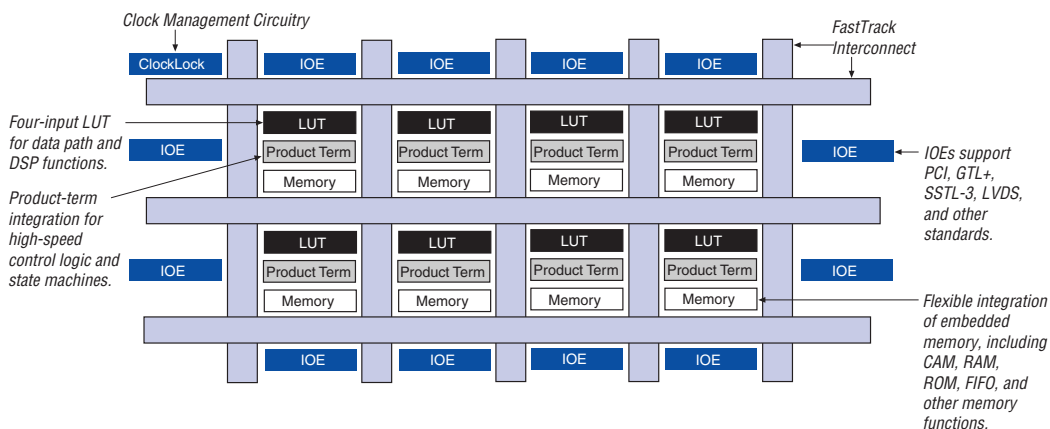
APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack[®] Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires.

Figure 1 shows an overview of the APEX 20K device.

Figure 1. APEX 20K Device Block Diagram



APEX 20K devices provide two dedicated clock pins and four dedicated input pins that drive register control inputs. These signals ensure efficient distribution of high-speed, low-skew control signals. These signals use dedicated routing channels to provide short delays and low skews. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or internally generated asynchronous clear signals with high fan-out. The dedicated clock pins featured on the APEX 20K devices can also feed logic. The devices also feature ClockLock and ClockBoost clock management circuitry. APEX 20KE devices provide two additional dedicated clock pins, for a total of four dedicated clock pins.

MegaLAB Structure

APEX 20K devices are constructed from a series of MegaLAB™ structures. Each MegaLAB structure contains a group of logic array blocks (LABs), one ESB, and a MegaLAB interconnect, which routes signals within the MegaLAB structure. The EP20K30E device has 10 LABs, EP20K60E through EP20K600E devices have 16 LABs, and the EP20K1000E and EP20K1500E devices have 24 LABs. Signals are routed between MegaLAB structures and I/O pins via the FastTrack Interconnect. In addition, edge LABs can be driven by I/O pins through the local interconnect. Figure 2 shows the MegaLAB structure.

Figure 2. MegaLAB Structure

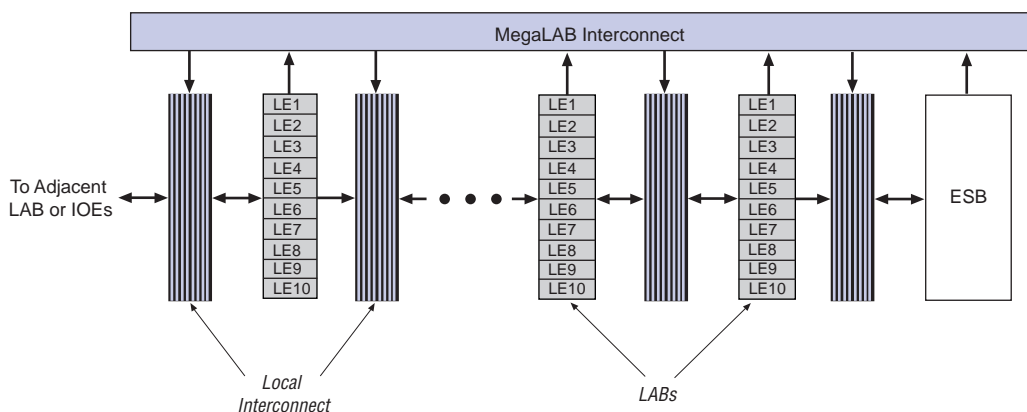
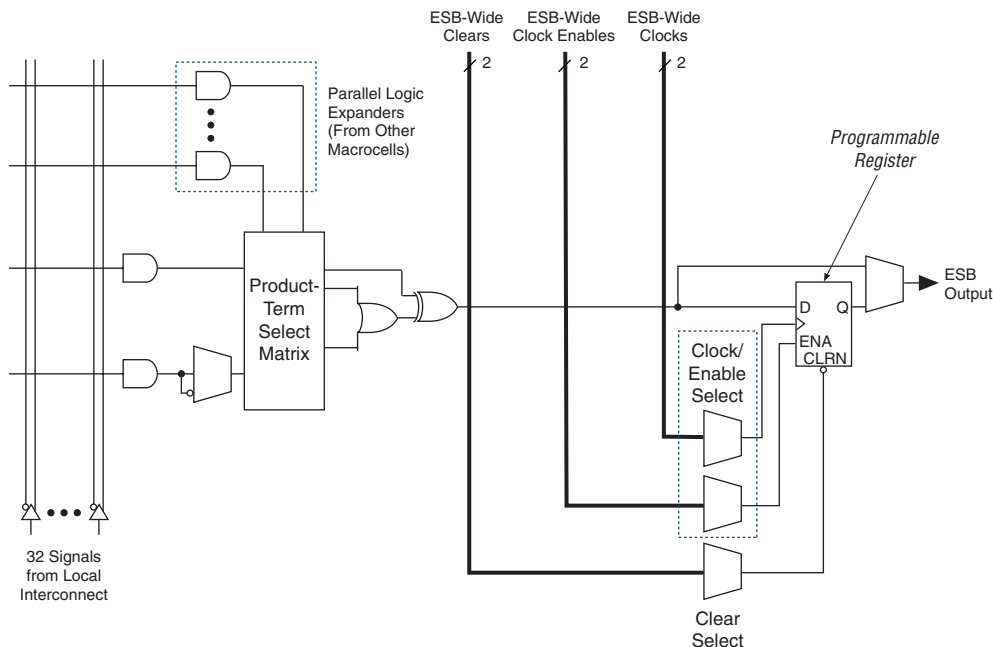


Figure 14. APEX 20K Macrocell



For registered functions, each macrocell register can be programmed individually to implement D, T, JK, or SR operation with programmable clock control. The register can be bypassed for combinatorial operation. During design entry, the designer specifies the desired register type; the Quartus II software then selects the most efficient register operation for each registered function to optimize resource utilization. The Quartus II software or other synthesis tools can also select the most efficient register operation automatically when synthesizing HDL designs.

Each programmable register can be clocked by one of two ESB-wide clocks. The ESB-wide clocks can be generated from device dedicated clock pins, global signals, or local interconnect. Each clock also has an associated clock enable, generated from the local interconnect. The clock and clock enable signals are related for a particular ESB; any macrocell using a clock also uses the associated clock enable.

If both the rising and falling edges of a clock are used in an ESB, both ESB-wide clock signals are used.

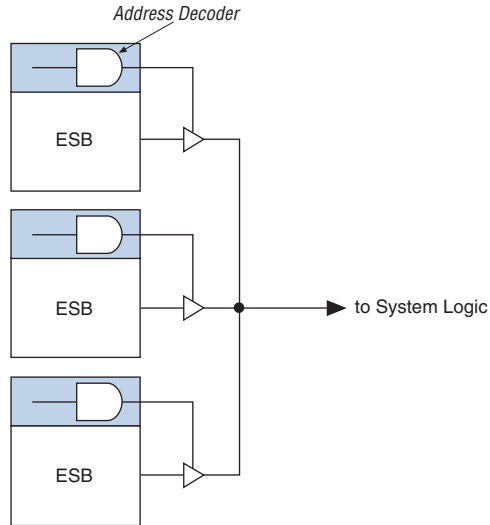
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (\overline{WE}) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the \overline{WE} signal. In contrast, the ESB's synchronous RAM generates its own \overline{WE} signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128×16 , 256×8 , 512×4 , $1,024 \times 2$, or $2,048 \times 1$. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128×16 RAM blocks can be combined to form a 128×32 RAM block, and two 512×4 RAM blocks can be combined to form a 512×8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

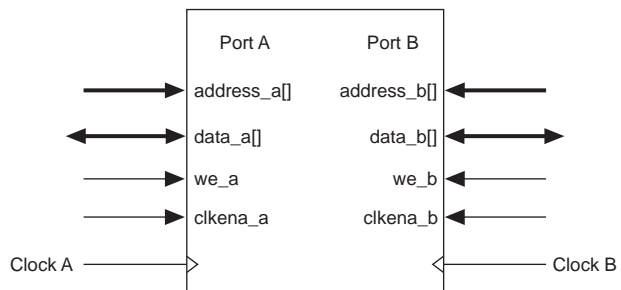
To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See [Figure 18](#).

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in [Figure 19](#).

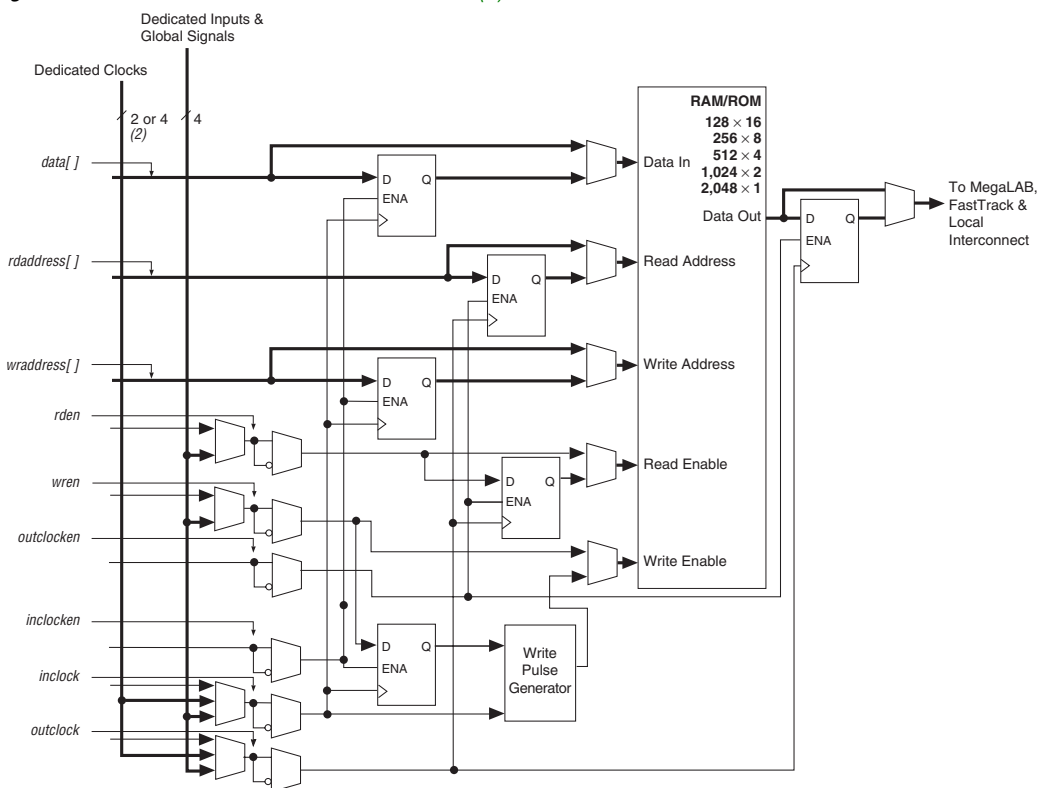
Figure 19. APEX 20K ESB Implementing Dual-Port RAM



Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

Figure 20. ESB in Read/Write Clock Mode *Note (1)*



Notes to Figure 20:

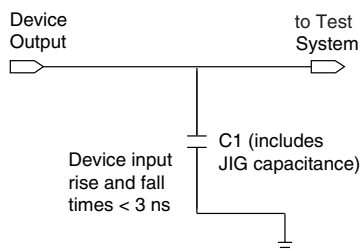
- (1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
- (2) APEX 20KE devices have four dedicated clocks.

APEX 20KE devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KE IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KE IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II software compiler can set these delays automatically to minimize setup time while providing a zero hold time.

Table 11 describes the APEX 20KE programmable delays and their logic options in the Quartus II software.

Table 11. APEX 20KE Programmable Delay Chains	
Programmable Delays	Quartus II Logic Option
Input Pin to Core Delay	Decrease input delay to internal cells
Input Pin to Input Register Delay	Decrease input delay to input registers
Core to Output Register Delay	Decrease input delay to output register
Output Register t_{CO} Delay	Increase delay to output pin
Clock Enable Delay	Increase clock enable delay

The register in the APEX 20KE IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. **Figure 26** shows how fast bidirectional I/O pins are implemented in APEX 20KE devices. This feature is useful for cases where the APEX 20KE device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 32. APEX 20K AC Test Conditions *Note (1)*


Note to Figure 32:

- (1) Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result.

Operating Conditions

Tables 23 through 26 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V APEX 20K devices.

Table 23. APEX 20K 5.0-V Tolerant Device Absolute Maximum Ratings *Notes (1), (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground (3)	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I			–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	°C
T_{AMB}	Ambient temperature	Under bias	–65	135	°C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	°C
		Ceramic PGA packages, under bias		150	°C

All specifications are always representative of worst-case supply voltage and junction temperature conditions. All output-pin-timing specifications are reported for maximum driver strength.

Figure 36 shows the f_{MAX} timing model for APEX 20K devices.

Figure 36. APEX 20K t_{MAX} Timing Model

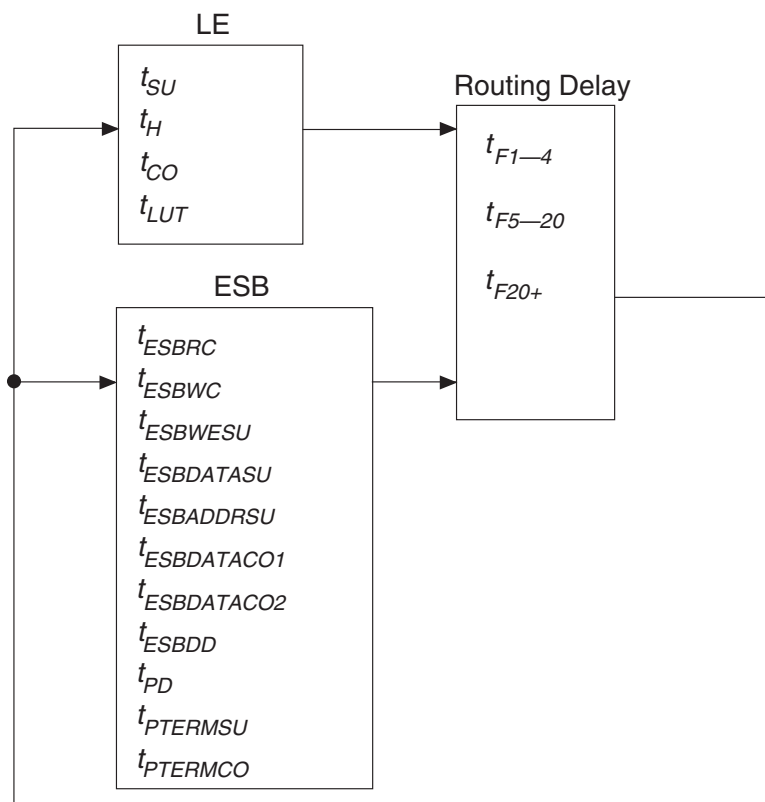


Figure 37 shows the f_{MAX} timing model for APEX 20KE devices. These parameters can be used to estimate f_{MAX} for multiple levels of logic. Quartus II software timing analysis should be used for more accurate timing information.

Table 31. APEX 20K t_{MAX} Timing Parameters (Part 2 of 2)

Symbol	Parameter
$t_{ESB\text{DATA}CO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay
t_{F1-4}	Fanout delay using local interconnect
t_{F5-20}	Fanout delay using MegaLab Interconnect
t_{F20+}	Fanout delay using FastTrack Interconnect
t_{CH}	Minimum clock high time from clock pin
t_{CL}	Minimum clock low time from clock pin
t_{CLRP}	LE clear pulse width
t_{PREP}	LE preset pulse width
t_{ESBCH}	Clock high time
t_{ESBCL}	Clock low time
t_{ESBWP}	Write pulse width
t_{ESBRP}	Read pulse width

Tables 32 and 33 describe APEX 20K external timing parameters.

Table 32. APEX 20K External Timing Parameters Note (1)

Symbol	Clock Parameter
t_{INSU}	Setup time with global clock at IOE register
t_{INH}	Hold time with global clock at IOE register
t_{OUTCO}	Clock-to-output delay with global clock at IOE register

Table 33. APEX 20K External Bidirectional Timing Parameters Note (1)

Symbol	Parameter	Conditions
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{INH\text{BIDIR}}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{OUTCO\text{BIDIR}}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 10 pF
$t_{XZ\text{BIDIR}}$	Synchronous IOE output buffer disable delay	C1 = 10 pF
$t_{Z\text{BIDIR}}$	Synchronous IOE output buffer enable delay, slow slew rate = off	C1 = 10 pF

Table 41. EP20K200 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_H	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.7		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.4		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Table 76. EP20K200E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{CH}	1.36		2.44		2.65		ns
t _{CL}	1.36		2.44		2.65		ns
t _{CLRP}	0.18		0.19		0.21		ns
t _{PREP}	0.18		0.19		0.21		ns
t _{ESBCH}	1.36		2.44		2.65		ns
t _{ESBCL}	1.36		2.44		2.65		ns
t _{ESBWP}	1.18		1.48		1.76		ns
t _{ESBRP}	0.95		1.17		1.41		ns

Table 77. EP20K200E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSU}	2.24		2.35		2.47		ns
t _{INH}	0.00		0.00		0.00		ns
t _{OUTCO}	2.00	5.12	2.00	5.62	2.00	6.11	ns
t _{INSUPLL}	2.13		2.07		-		ns
t _{INHPLL}	0.00		0.00		-		ns
t _{OUTCOPLL}	0.50	3.01	0.50	3.36	-	-	ns

Table 80. EP20K300E t_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.79		2.44		3.25	ns
t_{ESBSRC}		2.40		3.12		4.01	ns
t_{ESBAWC}		3.41		4.65		6.20	ns
t_{ESBSWC}		3.68		4.68		5.93	ns
$t_{ESBWASU}$	1.55		2.12		2.83		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.71		2.33		3.11		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.72		2.34		3.13		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.63		2.36		3.28		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.07		0.39		0.80		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.27		0.67		1.17		ns
$t_{ESBRADDRSU}$	0.34		0.75		1.28		ns
$t_{ESBDATACO1}$		1.03		1.20		1.40	ns
$t_{ESBDATACO2}$		2.33		3.18		4.24	ns
t_{ESBDD}		3.41		4.65		6.20	ns
t_{PD}		1.68		2.29		3.06	ns
$t_{PTERMSU}$	0.96		1.48		2.14		ns
$t_{PTERMCO}$		1.05		1.22		1.42	ns

Table 81. EP20K300E t_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.22		0.24		0.26	ns
t_{F5-20}		1.33		1.43		1.58	ns
t_{F20+}		3.63		3.93		4.35	ns

Table 92. EP20K600E t_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.67		2.39		3.11	ns
t_{ESBSRC}		2.27		3.07		3.86	ns
t_{ESBAWC}		3.19		4.56		5.93	ns
t_{ESBSWC}		3.51		4.62		5.72	ns
$t_{ESBWASU}$	1.46		2.08		2.70		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.60		2.29		2.97		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.61		2.30		2.99		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.49		2.30		3.11		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.01		0.35		0.71		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.19		0.62		1.06		ns
$t_{ESBRADDRSU}$	0.25		0.71		1.17		ns
$t_{ESBDATAO1}$		1.01		1.19		1.37	ns
$t_{ESBDATAO2}$		2.18		3.12		4.05	ns
t_{ESBDD}		3.19		4.56		5.93	ns
t_{PD}		1.57		2.25		2.92	ns
$t_{PTERMSU}$	0.85		1.43		2.01		ns
$t_{PTERMCO}$		1.03		1.21		1.39	ns

Table 93. EP20K600E t_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.22		0.25		0.26	ns
t_{F5-20}		1.26		1.39		1.52	ns
t_{F20+}		3.51		3.88		4.26	ns

Table 108. EP20K1500E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	3.47		3.68		3.99		ns
t_{INHBIDIR}	0.00		0.00		0.00		ns
$t_{\text{OUTCOBIDIR}}$	2.00	6.18	2.00	6.81	2.00	7.36	ns
t_{XZBIDIR}		6.91		7.62		8.38	ns
t_{ZXBIDIR}		6.91		7.62		8.38	ns
$t_{\text{INSUBIDIRPLL}}$	3.05		3.26				ns
$t_{\text{INHBIDIRPLL}}$	0.00		0.00				ns
$t_{\text{OUTCOBIDIRPLL}}$	0.50	2.67	0.50	2.99			ns
$t_{\text{XZBIDIRPLL}}$		3.41		3.80			ns
$t_{\text{ZXBIDIRPLL}}$		3.41		3.80			ns

Tables 109 and 110 show selectable I/O standard input and output delays for APEX 20KE devices. If you select an I/O standard input or output delay other than LVCMOS, add or subtract the selected speed grade to or from the LVCMOS value.

Table 109. Selectable I/O Standard Input Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.04		0.05	ns
1.8 V		-0.11		0.03		0.04	ns
PCI		0.01		0.09		0.10	ns
GTL+		-0.24		-0.23		-0.19	ns
SSTL-3 Class I		-0.32		-0.21		-0.47	ns
SSTL-3 Class II		-0.08		0.03		-0.23	ns
SSTL-2 Class I		-0.17		-0.06		-0.32	ns
SSTL-2 Class II		-0.16		-0.05		-0.31	ns
LVDS		-0.12		-0.12		-0.12	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

SRAM configuration elements allow APEX 20K devices to be reconfigured in-circuit by loading new configuration data into the device. Real-time reconfiguration is performed by forcing the device into command mode with a device pin, loading different configuration data, reinitializing the device, and resuming user-mode operation. In-field upgrades can be performed by distributing new configuration files.

Configuration Schemes

The configuration data for an APEX 20K device can be loaded with one of five configuration schemes (see Table 111), chosen on the basis of the target application. An EPC2 or EPC16 configuration device, intelligent controller, or the JTAG port can be used to control the configuration of an APEX 20K device. When a configuration device is used, the system can configure automatically at system power-up.

Multiple APEX 20K devices can be configured in any of five configuration schemes by connecting the configuration enable (nCE) and configuration enable output (nCEO) pins on each device.

Table 111. Data Sources for Configuration	
Configuration Scheme	Data Source
Configuration device	EPC1, EPC2, EPC16 configuration devices
Passive serial (PS)	MasterBlaster or ByteBlasterMV download cable or serial data source
Passive parallel asynchronous (PPA)	Parallel data source
Passive parallel synchronous (PPS)	Parallel data source
JTAG	MasterBlaster or ByteBlasterMV download cable or a microprocessor with a Jam or JBC File



For more information on configuration, see *Application Note 116 (Configuring APEX 20K, FLEX 10K, & FLEX 6000 Devices.)*

Device Pin-Outs

See the Altera web site (<http://www.altera.com>) or the *Altera Digital Library* for pin-out information

Revision History

The information contained in the *APEX 20K Programmable Logic Device Family Data Sheet* version 5.1 supersedes information published in previous versions.

Version 5.1

APEX 20K Programmable Logic Device Family Data Sheet version 5.1 contains the following changes:

- In version 5.0, the VI input voltage spec was updated in Table 28 on page 63.
- In version 5.0, *Note (5)* to Tables 27 through 30 was revised.
- Added *Note (2)* to Figure 21 on page 33.

Version 5.0

APEX 20K Programmable Logic Device Family Data Sheet version 5.0 contains the following changes:

- Updated Tables 23 through 26. Removed 2.5-V operating condition tables because all APEX 20K devices are now 5.0-V tolerant.
- Updated conditions in Tables 33, 38 and 39.
- Updated data for $t_{ESB\text{DATAH}}$ parameter.

Version 4.3

APEX 20K Programmable Logic Device Family Data Sheet version 4.3 contains the following changes:

- Updated Figure 20.
- Updated *Note (2)* to Table 13.
- Updated notes to Tables 27 through 30.

Version 4.2

APEX 20K Programmable Logic Device Family Data Sheet version 4.2 contains the following changes:

- Updated Figure 29.
- Updated *Note (1)* to Figure 29.

Version 4.1

APEX 20K Programmable Logic Device Family Data Sheet version 4.1 contains the following changes:

- t_{ESBWEH} added to [Figure 37](#) and [Tables 35, 50, 56, 62, 68, 74, 86, 92, 97, and 104](#).
- Updated EP20K300E device internal and external timing numbers in [Tables 79 through 84](#).